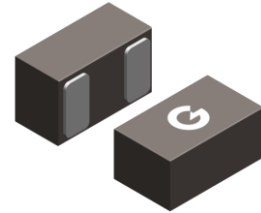
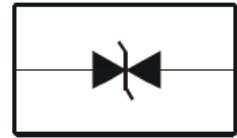


Features

- Low leakage current
- Working voltage: $V_{RWM} = 18V$
- Halogen free
- Qualified to AEC-Q101 standards for high reliability
- ESD / transient protection of high speed data lines
 - IEC 61000-4-2 (ESD): ± 30 kV (air), ± 25 kV (contact)

HF



DFN1006-2

Mechanical Data

- Case: DFN1006-2
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
TGESD18VBL	DFN1006-2	10000 pcs / Tape & Reel	18B

Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
IEC 61000-4-2; ESD (Air)	V_{ESD-A}	± 30	kV
IEC 61000-4-2; ESD (Contact)	V_{ESD-C}	± 25	kV
Reverse Stand-off Voltage	V_{RWM}	18	V
Peak Pulse Power ($t_p = 8/20\mu\text{s}$)	P_{PP}	300	W
Peak Pulse Current ($t_p = 8/20\mu\text{s}$)	I_{PP}	7	A

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation	P_D	0.25	W
Thermal Resistance Junction-to-Air	$R_{\theta JA}$	500	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Lead	$R_{\theta JL}$	255	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	300	$^\circ\text{C/W}$
Operating Temperature	T_J	-55 ~ +125	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage	V_{BR}	$I_T = 1\text{mA}$	20	-	25	V
Reverse Leakage Current	I_R	$V_{RWM} = 18\text{V}$	-	-	0.2	μA
Clamping Voltage	V_C	$I_{PP} = 1\text{A}$, ($t_p = 8/20\mu\text{s}$)	-	-	28	V
		$I_{PP} = 7\text{A}$, ($t_p = 8/20\mu\text{s}$)	-	-	40	V
Diode Capacitance	C_J	$V_R = 0\text{V}$, $f = 1\text{MHz}$	-	-	20	pF

Ratings and Characteristic Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

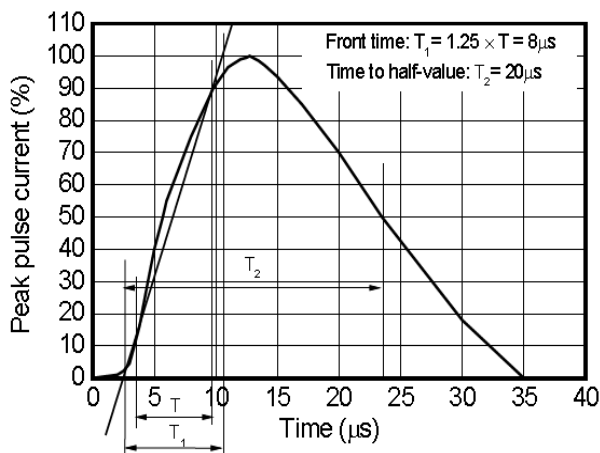


Fig 1 8/20 μs waveform per IEC61000-4-5

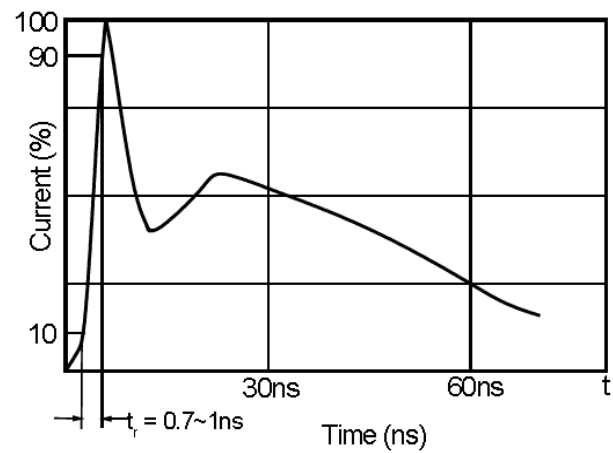


Fig 2 ESD pulse waveform according to IEC61000-4-2

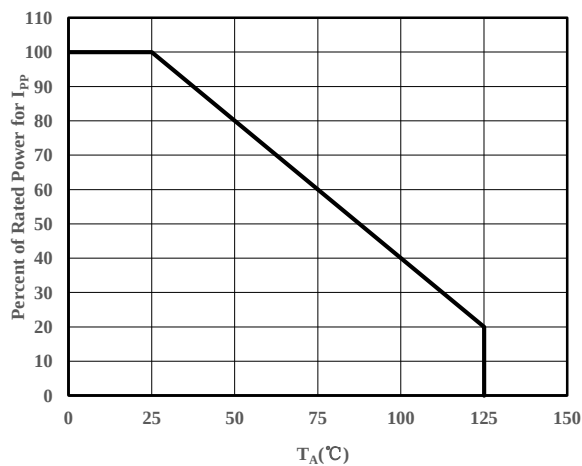


Fig 3 Power Derating Curve

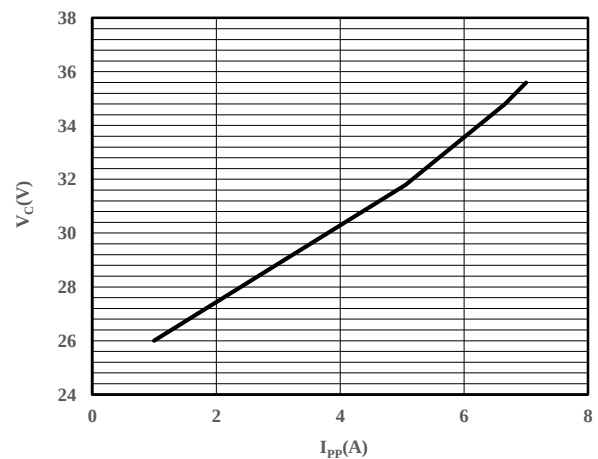


Fig 4 Clamping Voltage vs. Peak Pulse Current

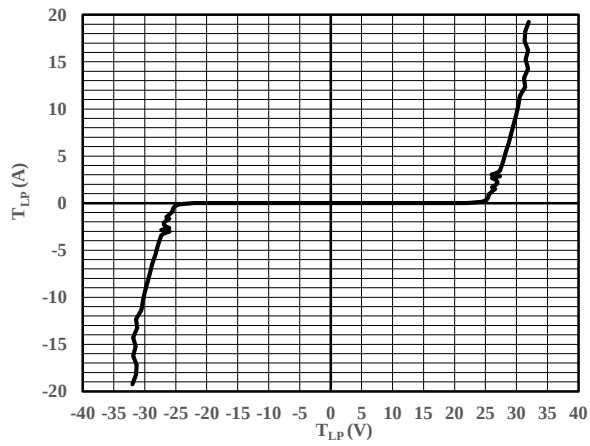
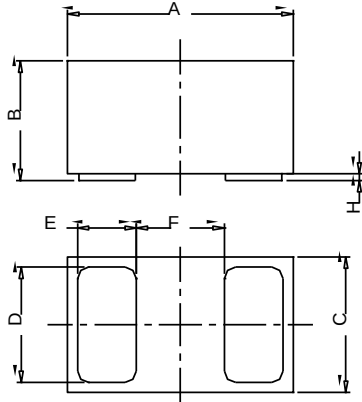


Fig 5 TLP Measurement

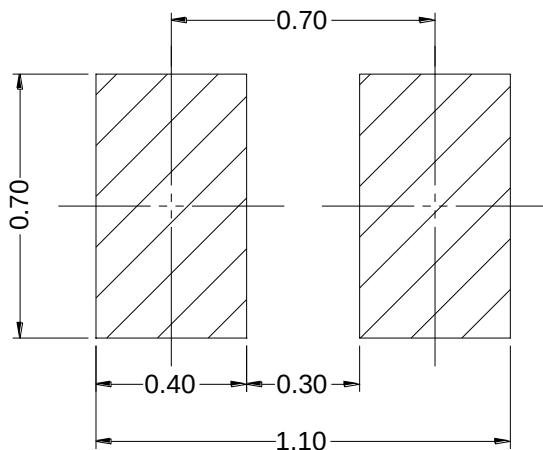
Package Outline Dimensions (Unit: mm)



DFN1006-2			
Dimension	Min.	Typ.	Max.
A	0.95	1.00	1.075
B	0.47	0.50	0.53
C	0.55	0.60	0.675
D	0.45	0.50	0.55
E	0.20	0.25	0.30
F	-	0.40	-
H	0	0.03	0.05

Package Outline Dimensions (Unit: mm)

DFN1006-2



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